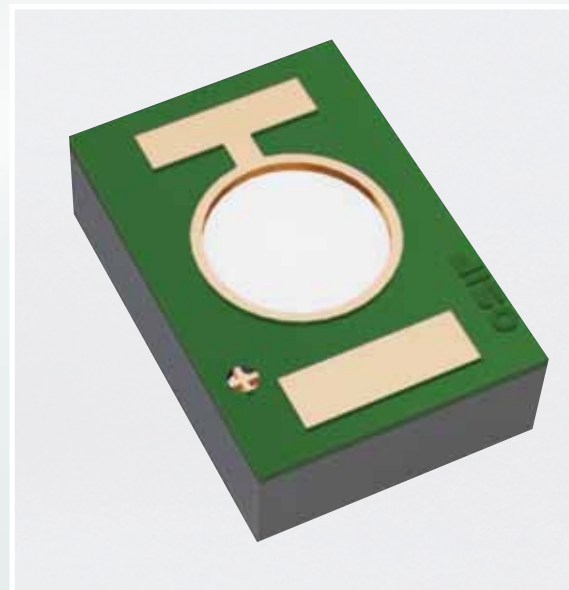


FCI-InGaAs-300B1XX

Back Illuminated InGaAs Photodiode / Arrays

FCI-InGaAs-300B1XX series are multifunctional backside illuminated photodiode/arrays. They come standard in a single element diode or 4- or 8- elements array with active area of 300 μ m. These back illuminated InGaAs photodiode/arrays are designed to be flip chip mounted to an optical plane for front or back illumination. They can be traditionally mounted (active area facing up), or assembled face down minimizing the overall dimensions. These low inductance, low dark current, and low capacitance back illuminated photodiode/arrays come with or without ceramic substrates.



APPLICATIONS

- High Speed Optical Communications
- Multichannel Fiber Optic Receiver
- Power Monitoring
- Single/Multi-Mode Fiber Optic Receiver
- Fast Ethernet, SONET/SDH OC-3/STM-1, ATM
- Instrumentation and Analog Receivers

FEATURES

- Back Illumination
- High Responsivity on Both Front and Back
- Low Noise
- Spectral Range 900nm to 1700nm

Electro-Optical Characteristics		$T_A=23^{\circ}\text{C}$, $V_R=5\text{V}$	
PARAMETERS	FCI-InGaAs-300B1	FCI-InGaAs-300B1X4	FCI-InGaAs-300B1X8
Active Area Diameter	300 μ m	300 μ m, Pitch:500 μ m	300 μ m, Pitch:500 μ m
Responsivity	Min. 0.85A/W @ 1550nm for both front and back Min. 0.80A/W @ 1310nm for both front and back		
Capacitance	Typ. 8pF, Max. 10pF @ $V_R=-5\text{V}$		
Dark Current	Typ. 0.05nA, Max. 5.0nA @ $V_R=-5\text{V}$		
Max. Reverse Voltage	15V		
Max. Reverse Current	5mA		
Max. Forward Current	25mA		
Bandwidth	Min. 100MHz		
Breakdown Voltage	Min. 10V @ 1 μ A		
Storage Temperature Range	From -40 to 85 $^{\circ}\text{C}$		
Operating Temperature Range	From 0 to 70 $^{\circ}\text{C}$		

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